

**INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION
(PTO-1449)**



ATTY. DOCKET NO.
005918 USA/
FPS/MMCS/APC

SERIAL NO.
09/943,955

APPLICANT
SHANMUGASUNDRAM et al.

FILING DATE
August 31, 2001

GROUP
1765

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
L.J.M-E	4,957,605	09/18/90	Hurwitt et al.			04/17/89
L.J.M-E	5,369,544	11/29/94	Mastrangelo			04/05/93
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EXAMINER

Lynette J. Ames-Euneni

DATE CONSIDERED

12/27/2004

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EXAMINER <i>Lynette J. Ung-Eumini</i>			DATE CONSIDERED 12/27/2004			

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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
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L.T.M.E.	Sun, S.C. 1998. "CVD and PVD Transition Metal Nitrides as Diffusion Barriers for Cu Metallization." <i>IEEE</i> . pp. 243-246.						
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EXAMINER <i>Lynette J. M...-E...</i>				DATE CONSIDERED <i>12/27/2004</i>			

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A circular black ink stamp from the Office of the Patent and Trademark Office. The text "OFFICE" is at the top, "PATENT & TRADEMARK OFFICE" is along the bottom curve, and the date "AUG 11 2004" is in the center.

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Lynette J. Ung-Evanni

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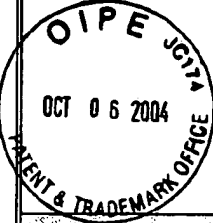
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)				
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